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2004
11/18/02
OFFICIALPATENT
Docket No. 150.00560104

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Lee et al.) Group Art Unit: 1765
Serial No.: 10/050,639) Examiner: D. Deo
Confirmation No.: 6476)
Filed: 15 January 2002)
For: METHOD AND COMPOSITION FOR SELECTIVELY ETCHING AGAINST
COBALT SILICIDE

AMENDMENT AND RESPONSE
UNDER 37 C.F.R. § 1.116

Assistant Commissioner for Patents
BOX AF
Washington D.C. 20231

Dear Sir:

In response to the Final Office Action dated 6 September 2002, please amend the above-identified application as follows:

In the Claims

Please add new claims 76-88; amend claims 46, 51, 53, and 55; and cancel claims 47-50. Per 37 C.F.R. § 1.121, amended claims are also shown in Appendix A with notations to indicate changes made (for convenience, all pending claims, including those added hereby, are provided in Appendix A).

46. (Once Amended) An etching method for use in integrated circuit fabrication, the method comprising:

providing a substrate assembly comprising a metal nitride region and a cobalt silicide region; and

selectively etching a portion of the metal nitride region against the cobalt silicide region using a solution comprising a mineral acid and a peroxide, wherein the solution etches the